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PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Docket No: Q95660

Katsumi KUSHIYA, et al.

Appln. No.: Based on PCT/JP04/019693

Confirmation No.: Unknown

Group Art Unit: Unknown

Filed: June 26, 2006

Examiner: Unknown

For:

INTEGRATED THIN-FILM SOLAR CELL AND PROCESS FOR PRODUCING THE

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §§ 1.97 and 1.98

MAIL STOP AMENDMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

In accordance with the duty of disclosure under 37 C.F.R. § 1.56, Applicant hereby notifies the U.S. Patent and Trademark Office of the documents which are listed on the attached PTO/SB/08 A & B (modified) form and/or listed herein and which the Examiner may deem material to patentability of the claims of the above-identified application.

One copy of each of the listed documents is submitted herewith, except for the following: U.S. patents and/or U.S. patent publications; and co-pending non-provisional U.S. applications filed after June 30, 2003.

The present Information Disclosure Statement is being filed: (1) No later than three months from the application's filing date; (2) Before the mailing date of the first Office Action on the merits (whichever is later); or (3) Before the mailing date of the first Office Action after

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INFORMATION DISCLOSURE STATEMENT

U.S. Appln. No.: Based on PCT/JP04/019693

Attorney Docket No.: Q95660

filing a request for continued examination (RCE) under §1.114, and therefore, no Statement

under 37 C.F.R. § 1.97(e) or fee under 37 C.F.R. § 1.17(p) is required.

In compliance with the concise explanation requirement under 37 C.F.R. § 1.98(a)(3) for

foreign language documents, Applicant encloses herewith a copy of a Communication from a

foreign patent office in a counterpart application citing such documents (International Search

Reprot for PCT/JP04/019693 dated March 15, 2005), together with an English-language version

(if not already included) of at least that portion of the Communication indicating the degree of

relevance found by the foreign patent office.

The submission of the listed documents is not intended as an admission that any such

document constitutes prior art against the claims of the present application. Applicant does not

waive any right to take any action that would be appropriate to antedate or otherwise remove any

listed document as a competent reference against the claims of the present application.

The USPTO is directed and authorized to charge all required fees, except for the Issue

Fee and the Publication Fee, to Deposit Account No. 19-4880. Please also credit any

overpayments to said Deposit Account.

Respectfully submitted,

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WASHINGTON OFFICE

23373

CUSTOMER NUMBER

Date: June 26, 2006

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D PTO/SB/08 A & B (08-03)

Based on PCT/JP04/019693

Unknown

June 26, 2006

Substitute for Form 1449 A & B/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)				First Named Inventor	Katsulli KOSHI I A	
				Art Unit	Unknown	
				Examiner Name	Unknown	
Sheet	1	of	1	Attorney Docket Number	Q95660	

Filing Date

Application Number

Confirmation Number

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Document Number		Publication Date		
		Number	Kind Code ² (if known)	MM-DD-YYYY	Name of Patentee or Applicant of Cited Documen	
		US 5,477,088	A	12-19-1995	Angus A. Rockett, et al.	
		US				
		US				
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FOREIGN PATENT DOCUMENTS								
Examiner Initials*	Cite No.1	Foreign Patent Document			Publication Date	Name of Patentee or		
		Country Code ³	Number⁴	Kind Code ⁵ (if known)	MM-DD-YYYY	Applicant of Cited Document	Translation ⁶	
	-,-	JP	2002-319686	Α	10-31-2002	Matsushita Electric Industrial Co., Ltd.		
		JP	10-200142	Á	07-31-1998	Yazaki Corp.		
		JP	4-94174	Α	03-26-1992	Fuji Electric Co., Ltd.		
		JР	2001-156026	A	06-08-2001	Canon Inc.	,	
		JP	11-345989	Α	12-14-1999	Matsushita Battery Industrial Co., Ltd.	,	
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Examiner Initials*	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.				
	-	T. WADA, et al., "Characterization of the Cu)In,Ga)Se ₂ /Mo interface in CIGS solar cells". Thin Solid Films, 2001, pp. 118-122, Vol. 387				
		J. ALVAREZ-GARCIA, et al., "Microstructure and secondary phases in coevaporated CulnS ₂ films: Dependence on growth temperature and chemical composition", Journal of Vacuum science & Technology A, January/February 2001, pp. 232-239, Vol. 19				
		International Search Report for PCT/JP04/019693 dated March 15, 2005				
			<u> </u>			

Examiner Signature		Date Considered	
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^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Applicant's unique citation designation number (optional). ²See Kind Codes of USPTO Patent Documents at www.uspto.gov, MPEP 901.04 or follow the hyperlink from the title of the document to the intranet. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST. 3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to indicate here if English language Translation is attached.